

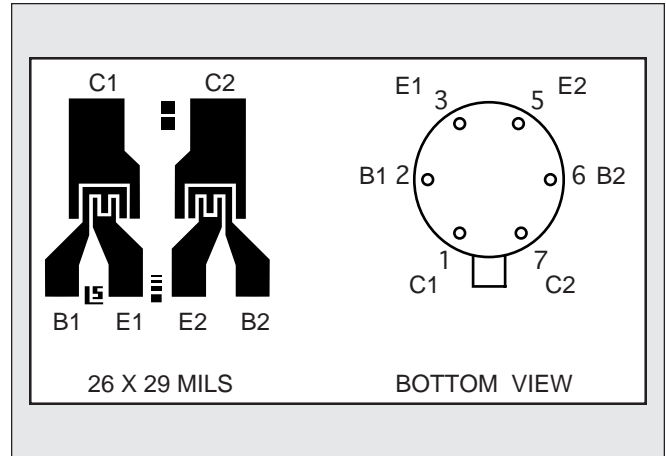
LINEAR SYSTEMS

Linear Integrated Systems

LS350 LS351 LS352

MONOLITHIC DUAL PNP TRANSISTORS

FEATURES		
HIGH GAIN		$h_{FE} \geq 200$ @ $10\mu\text{A} - 1\text{mA}$
TIGHT V_{BE} MATCHING		$ V_{BE1} - V_{BE2} = 0.2\text{mV TYP.}$
HIGH f_T		$275\text{MHz TYP. @ } 1\text{mA}$
ABSOLUTE MAXIMUM RATINGS NOTE 1		
@ 25°C (unless otherwise noted)		
I_C	Collector Current	10mA
Maximum Temperatures		
	Storage Temperature	-65° to $+200^\circ\text{C}$
	Operating Junction Temperature	$+150^\circ\text{C}$
Maximum Power Dissipation		
		ONE SIDE BOTH SIDES
	Device Dissipation @ Free Air	250mW 500mW
	Linear Derating Factor	$2.3\text{mW}/^\circ\text{C}$ $4.3\text{mW}/^\circ\text{C}$



ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

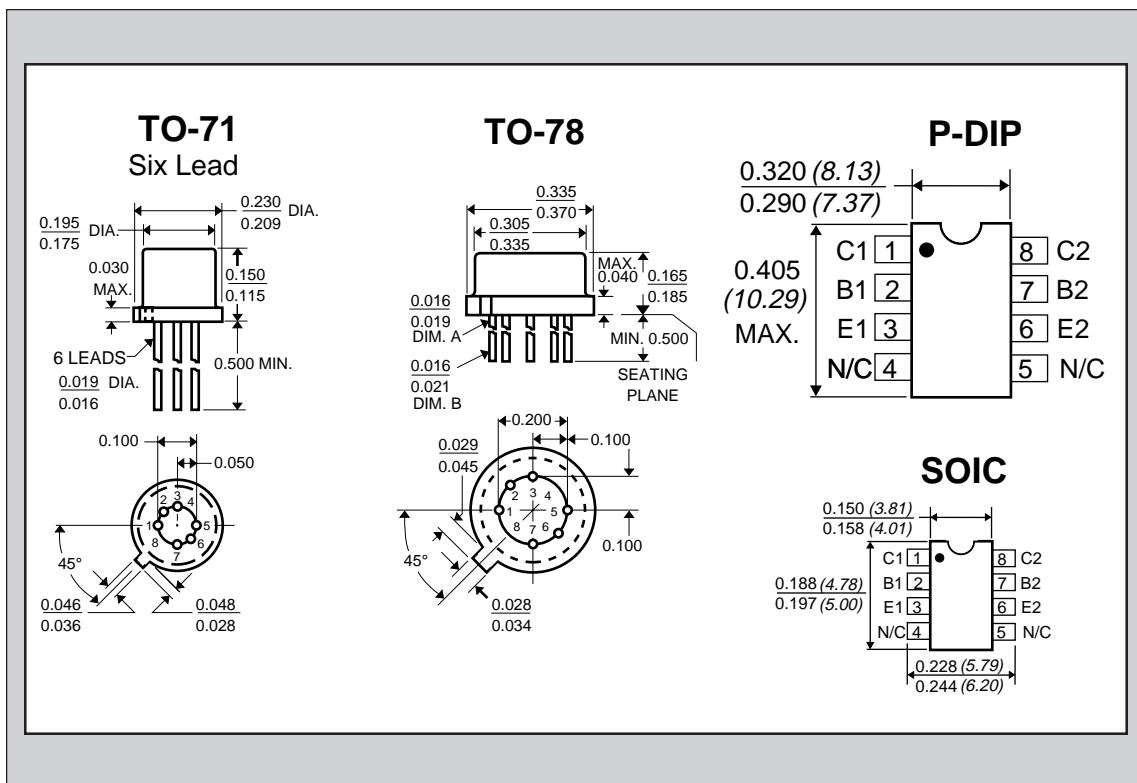
SYMBOL	CHARACTERISTICS	LS350	LS351	LS352		UNITS	CONDITIONS
V_{CBO}	Collector to Base Voltage	25	45	60	MIN.	V	$I_C = 10\mu\text{A}$ $I_E = 0$
V_{CEO}	Collector to Emitter Voltage	25	45	60	MIN.	V	$I_C = 10\mu\text{A}$ $I_B = 0$
V_{EBO}	Emitter to Base Voltage	6.2	6.2	6.2	MIN.	V	$I_E = 10\mu\text{A}$ $I_C = 0$ NOTE 2
V_{CCO}	Collector to Collector Voltage	30	60	100	MIN.	V	$I_C = 10\mu\text{A}$ $I_E = 0$
h_{FE}	DC Current Gain	100	150	200	MIN.		$I_C = 10\mu\text{A}$ $V_{CE} = 5\text{V}$
			600	600	MAX.		
h_{FE}	DC Current Gain	100	150	200	MIN.		$I_C = 100\mu\text{A}$ $V_{CE} = 5\text{V}$
			600	600	MAX.		
h_{FE}	DC Current Gain	100	150	200	MIN.		$I_C = 1\text{mA}$, $V_{CE} = 5\text{V}$
$V_{CE(SAT)}$	Collector Saturation Voltage	0.5	0.5	0.5	MAX.	V	$I_C = 1\text{mA}$ $I_B = 0.1\text{mA}$
I_{CBO}	Collector Cutoff Current	0.2	0.2	0.2	MAX.	nA	$I_E = 0$ $V_{CB} = \text{NOTE 3}$
I_{EBO}	Emitter Cutoff Current	0.2	0.2	0.2	MAX.	nA	$I_C = 0$ $V_{EB} = 3\text{V}$
C_{OBO}	Output Capacitance	2	2	2	MAX.	pF	$I_E = 0$ $V_{CB} = 5\text{V}$
C_{C1C2}	Collector to Collector Capacitance	2	2	2	MAX.	pF	$V_{CC} = 0$
I_{C1C2}	Collector to Collector Leakage Current	0.5	0.5	0.5	MAX.	nA	$V_{CC} = \text{NOTE 4}$
f_T	Current Gain Bandwidth Product	200	200	200	MIN.	MHz	$I_C = 1\text{mA}$ $V_{CE} = 5\text{V}$
NF	Narrow Band Noise Figure	3	3	3	MAX.	dB	$I_C = 100\mu\text{A}$ $V_{CE} = 5\text{V}$ $BW = 200\text{Hz}$ $R_G = 10\text{K}\Omega$ $f = 1\text{KHz}$

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MATCHING CHARACTERISTICS

SYMBOL	CHARACTERISTICS	LS350	LS351	LS352		UNITS	CONDITIONS
$ V_{BE1} - V_{BE2} $	Base Emitter Voltage Differential	1	0.4	0.2	TYP.	mV	$I_C = 10 \mu A$ $V_{CE} = 5V$
		5	1.0	0.5	MAX.	mV	
$\Delta (V_{BE1} - V_{BE2}) /^\circ C$	Base Emitter Voltage Differential Change with Temperature	2	1	0.5	TYP.	$\mu V/^\circ C$	$I_C = 10 \mu A$ $V_{CE} = 5V$
		20	10	2	MAX.	$\mu V/^\circ C$	$T_A = -55^\circ C$ to $+125^\circ C$
$ I_{B1} - I_{B2} $	Base Current Differential		5	5	MAX.	nA	$I_C = 10 \mu A$ $V_{CE} = 5V$
$ \Delta(I_{B1} - I_{B2}) /^\circ C$	Base Current Differential Change with Temperature		0.5	0.3	MAX.	nA/°C	$I_C = 10 \mu A$, $V_{CE} = 5V$ $T_A = -55^\circ C$ to $+125^\circ C$
h_{FE1}/h_{FE2}	DC Current Gain Differential	10	5	5	TYP.	%	$I_C = 10 \mu A$ $V_{CE} = 5V$



NOTES:

1. These ratings are limiting values above which the serviceability of any semiconductor may be impaired.
2. The reverse base-to-emitter voltage must never exceed 6.2 volts; the reverse base-to-emitter current must never exceed 10 μA .
3. For LS350: $V_{CB} = 20V$; for LS351 & LS352: $V_{CB} = 30V$.
4. For LS351: $V_{CC} = \pm 45V$; for LS352: $V_{CC} = \pm 80V$; for LS350: $V_{CC} = \pm 25V$.